

SUPPLEMENTARY INFORMATION

A Strategy of Stacking Double Absorbers to Gain High Efficiency in Silver Antimony Sulfide Selenide Based Thin Film Solar Cell

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SEM and EDS results for $\text{AgSb}(\text{S},\text{Se})_2$ based double absorbers with different combinations.

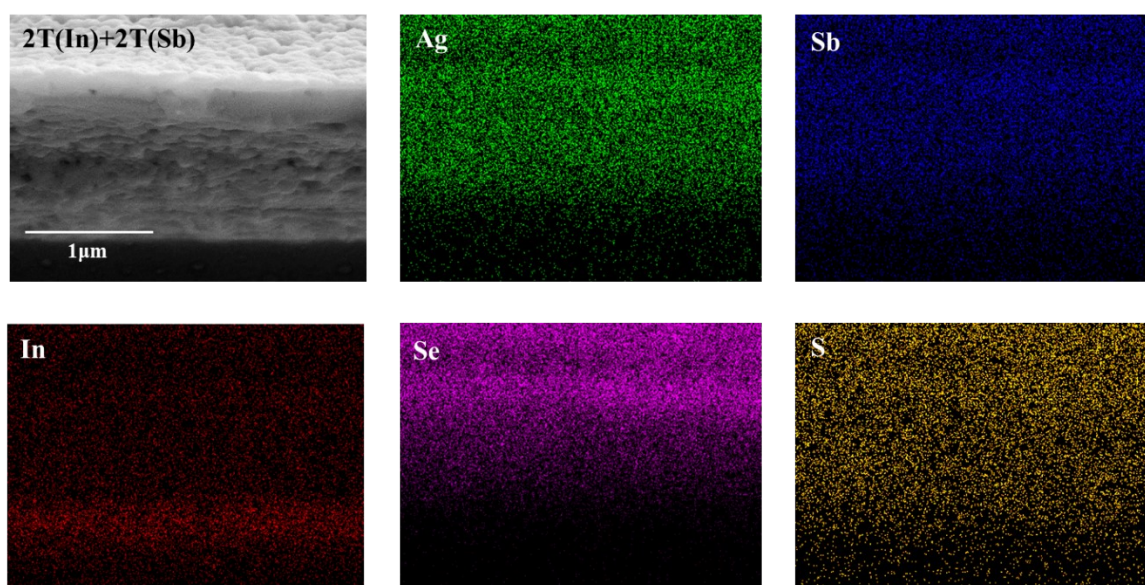


Figure S1 SEM picture of cross-section and EDS elemental maps for $2\text{T}(\text{In})+2\text{T}(\text{Sb})$

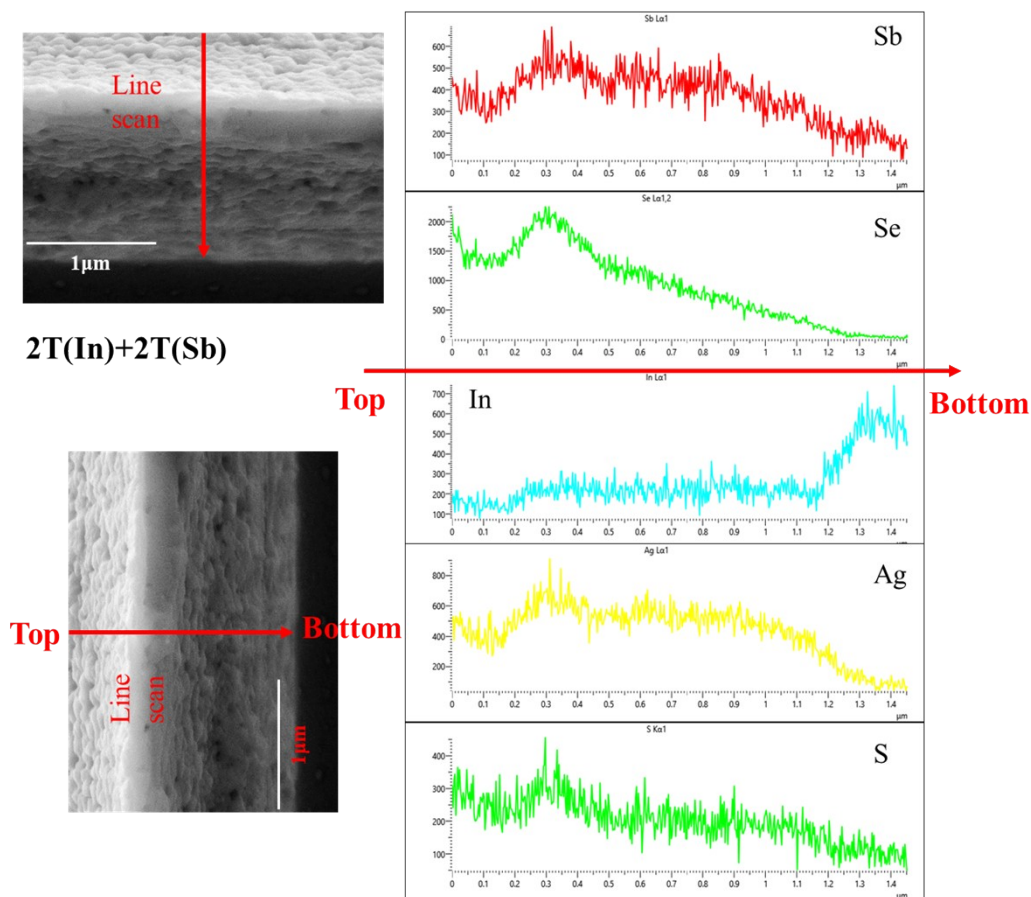


Figure S2 EDS line scan elemental distributions for cross-section of 2T(In)+2T(Sb)

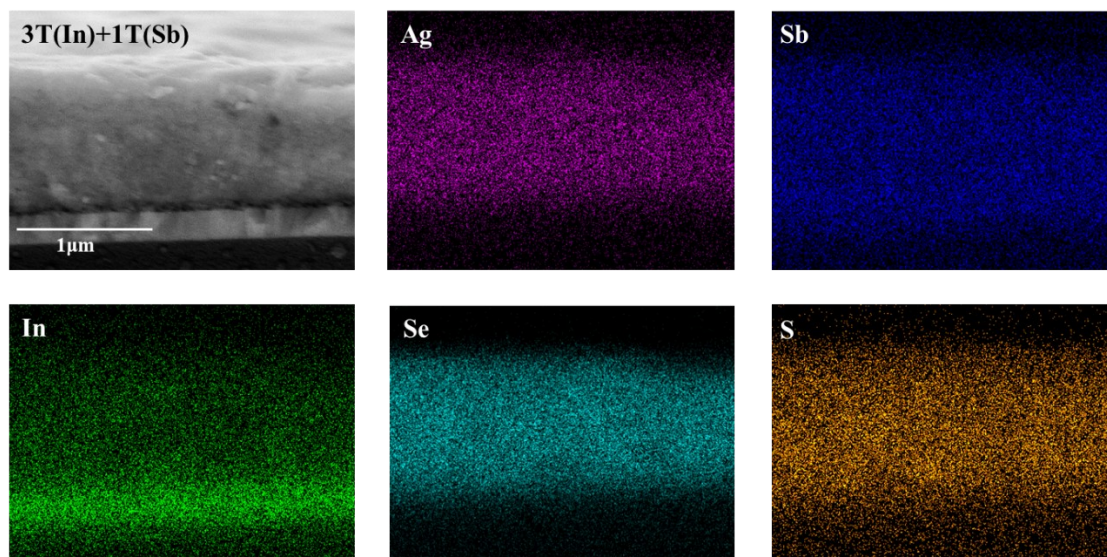


Figure S3 SEM picture of cross-section and EDS elemental maps for 3T(In)+1T(Sb)

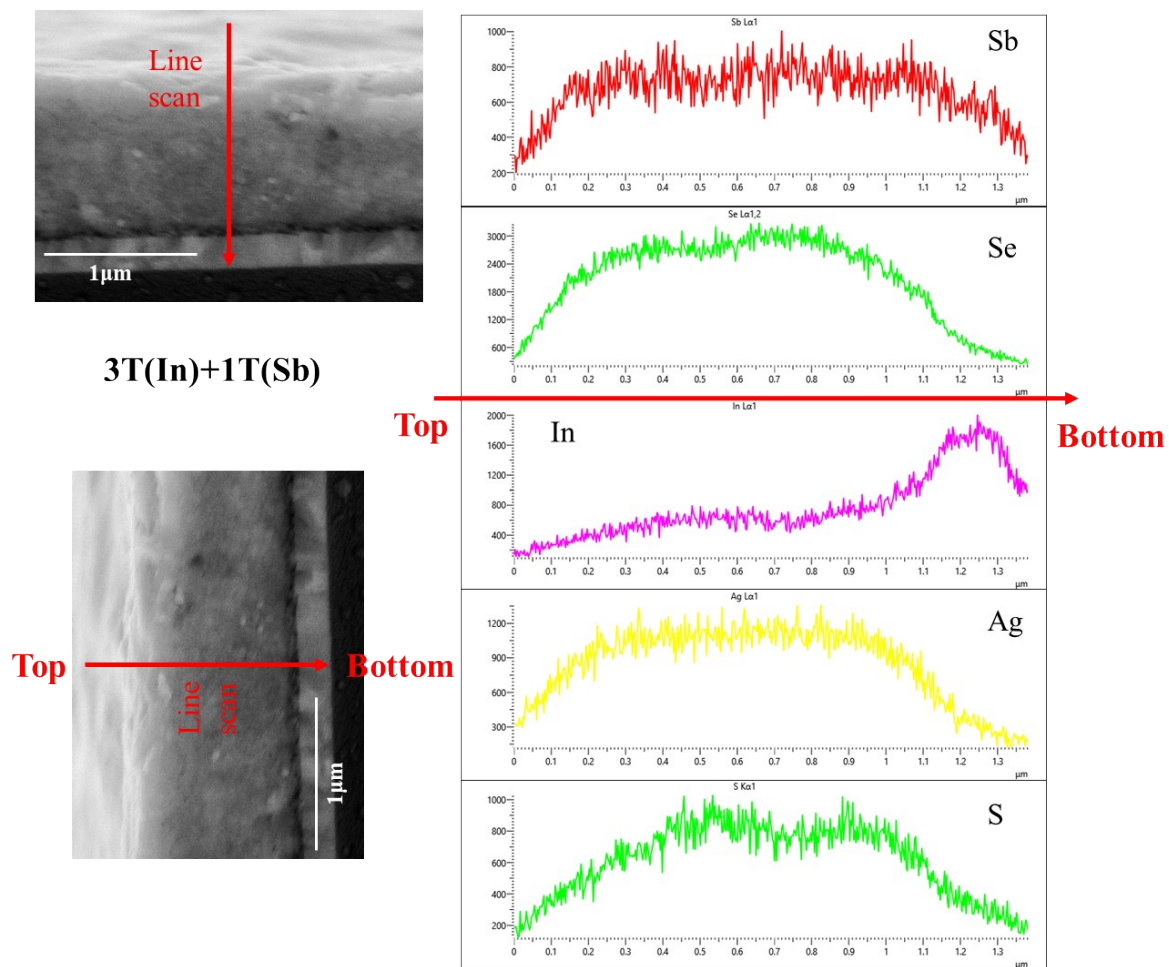


Figure S4 EDS line scan elemental distributions for cross-section of 3T(In)+1T(Sb)

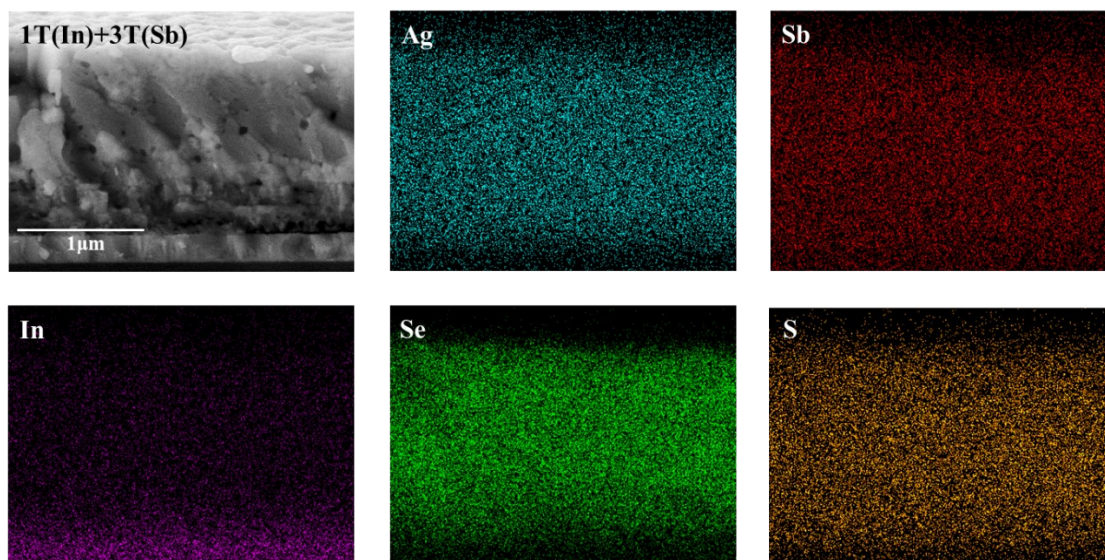


Figure S5 SEM picture of cross-section and EDS elemental maps for 1T(In)+3T(Sb)

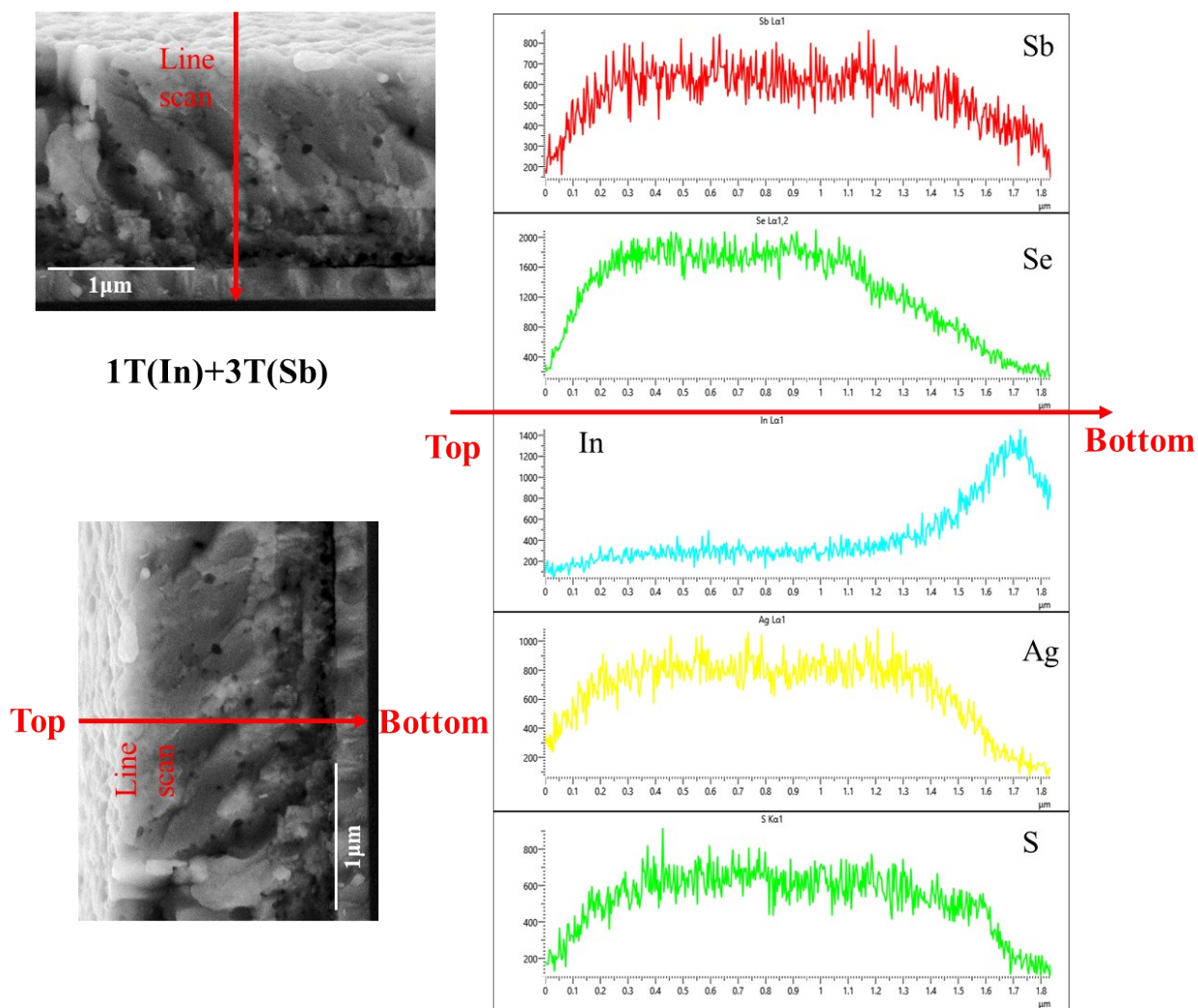


Figure S6 EDS line scan elemental distributions for cross-section of 1T(In)+3T(Sb)

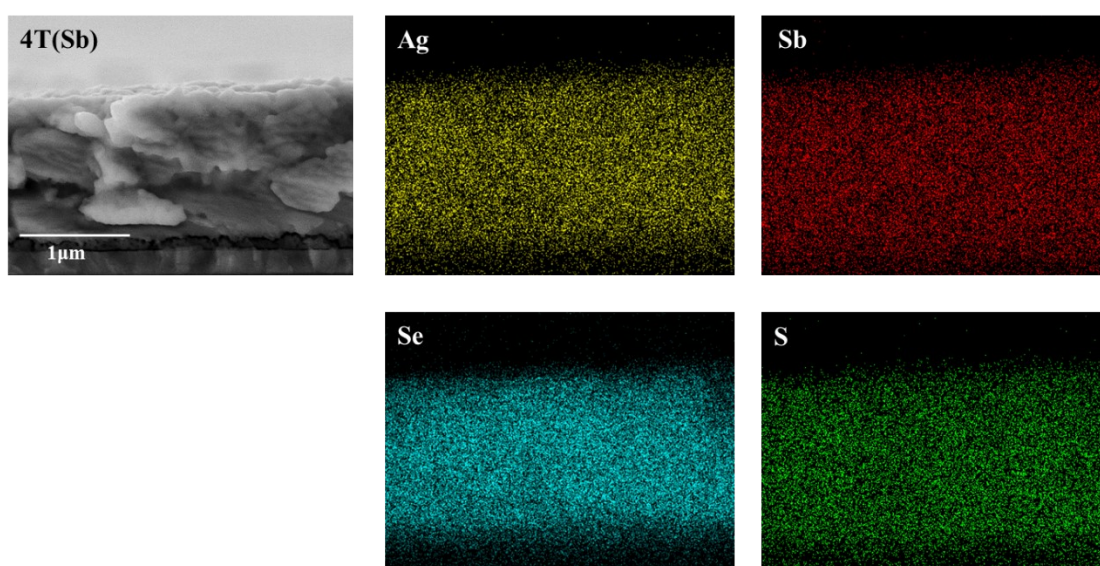


Figure S7 SEM picture of cross-section and EDS elemental maps for 4T(Sb)

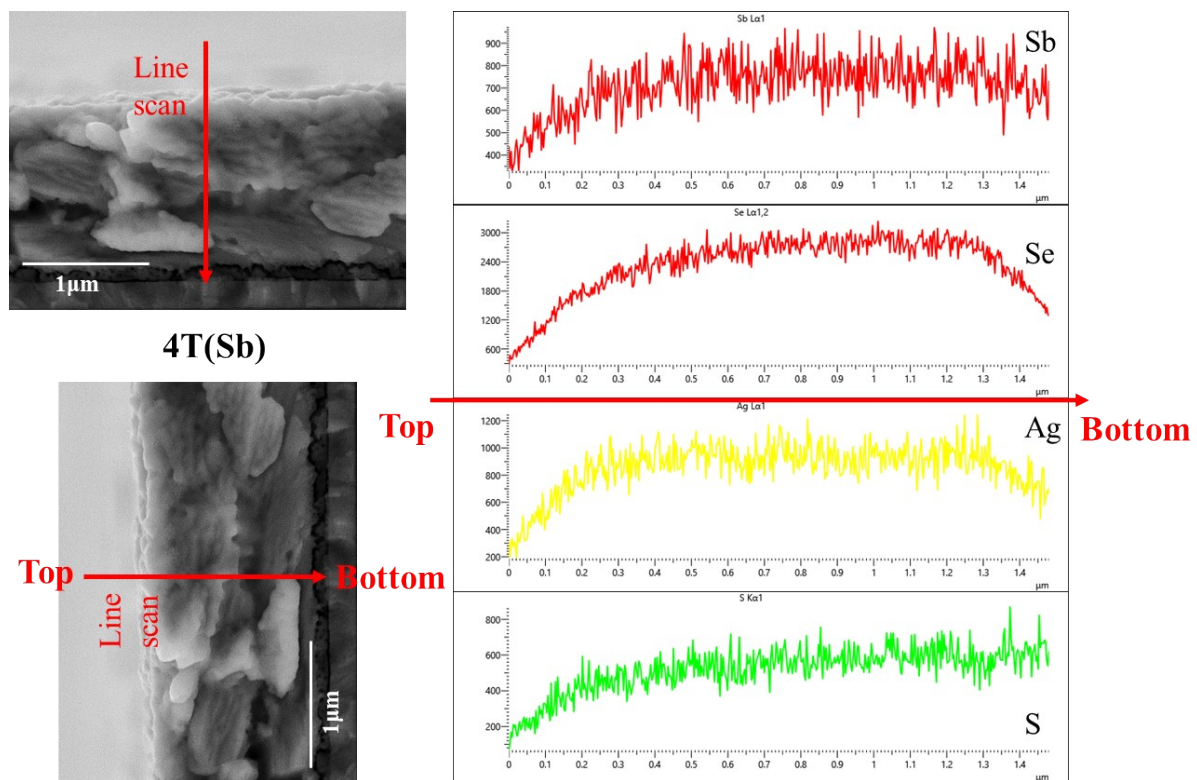


Figure S8 EDS line scan elemental distributions for cross-section of 4T(Sb)

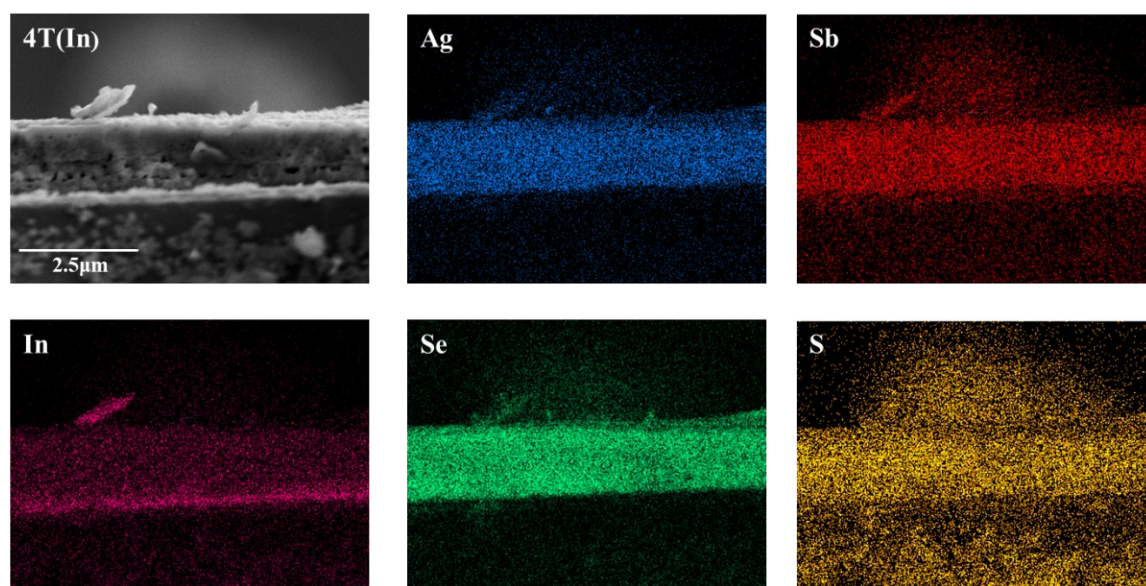
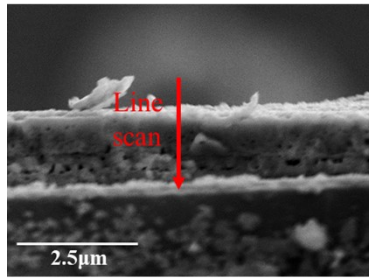


Figure S9 SEM picture of cross-section and EDS elemental maps for 4T(In)



4T(In)

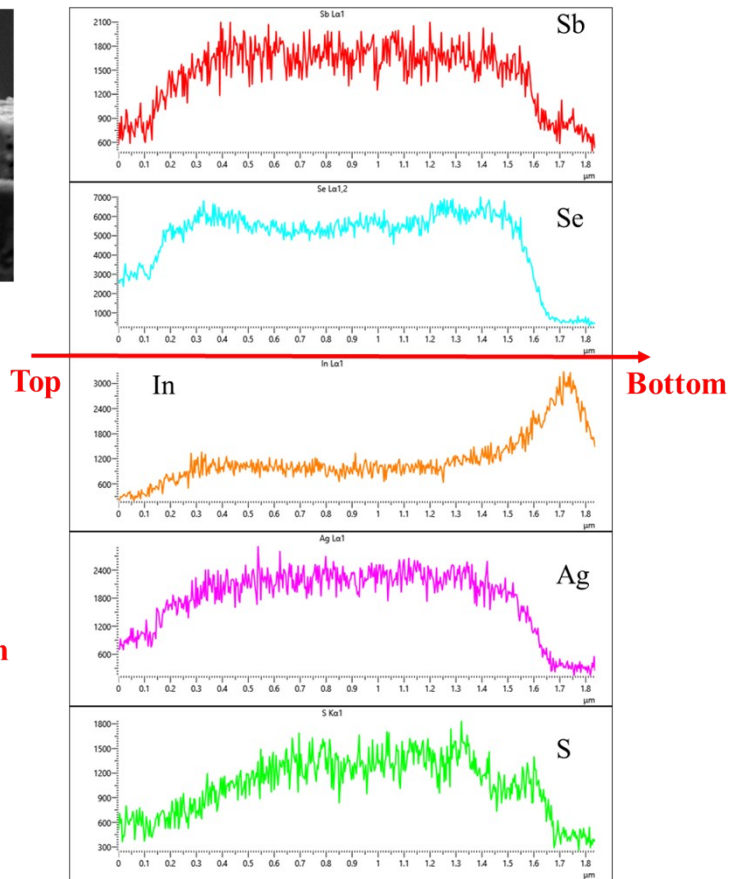
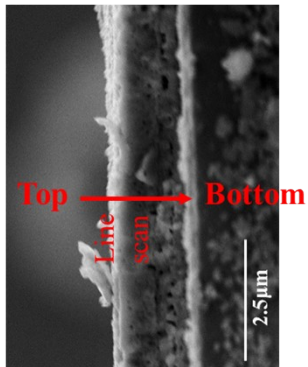


Figure S10 EDS line scan elemental distributions for cross-section of 4T(In)